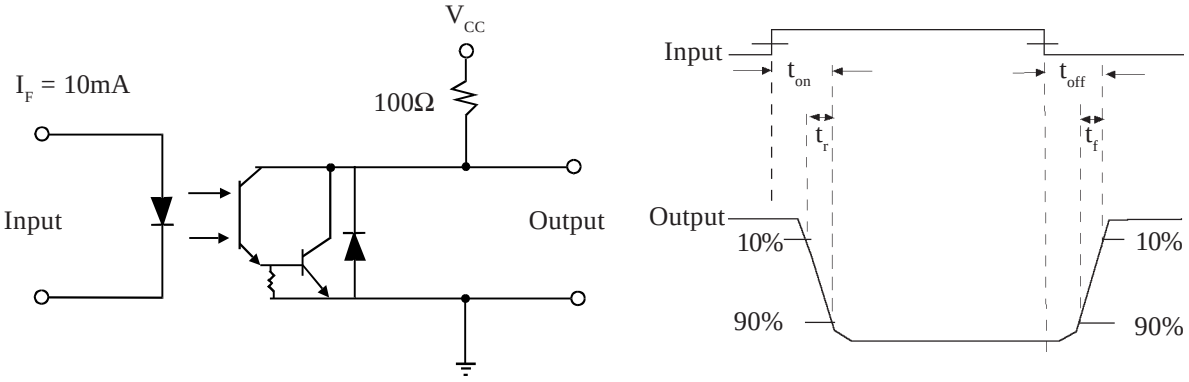
ELECTRICAL CHARACTERISTICS (T_A= 25°C Unless otherwise noted)

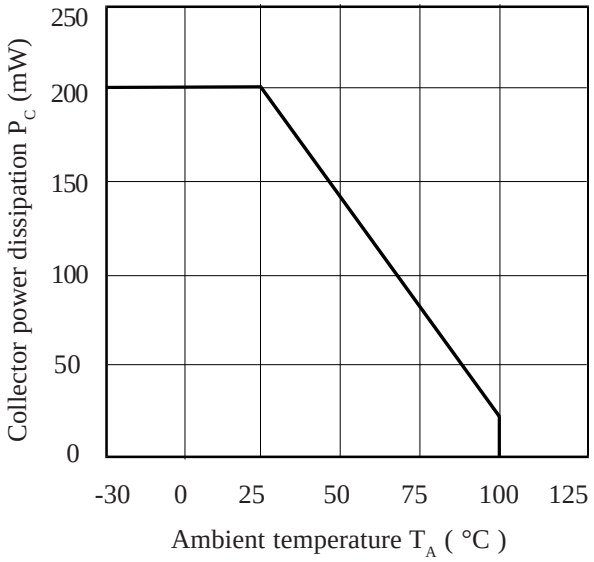
PARAMETER		MIN	TYP	MAX	UNITS	TEST CONDITION
Input	Forward Voltage (V_F)		1.2	1.5	V	I_F = 10mA
	Reverse Current (I_R)			10	µA	V_R=4V
Output	Collector-emitter Breakdown (BV_{CEO})					
	H11G1	100			V	I_C = 1mA
	H11G2	80			V	I_C = 1mA
	H11G3	55			V	I_C = 1mA
	Collector-base Breakdown (BV_{CBO})					
	H11G1	100			V	I_C = 100µA
	H11G2	80			V	I_C = 100µA
	H11G3	55			V	I_C = 100µA
	Emitter-base Breakdown (BV_{EBO})	6			V	I_E = 0.1mA
	Collector-emitter Dark Current (I_{CEO})					
	H11G1			100	nA	V_{CE} = 80V
	H11G2			100	nA	V_{CE} = 60V
	H11G3			100	nA	V_{CE} = 30V
Coupled	Collector Output Current (I_C)					
	H11G1,H11G2	100			mA	10mA I_F, 1.2V V_{CE}
	H11G1,H11G2	5			mA	1mA I_F, 5V V_{CE}
	H11G3	2			mA	1mA I_F, 5V V_{CE}
	Collector-emitter Saturation Voltage $V_{CE(SAT)}$					
	H11G1,H11G2			1.0	V	1mA I_F, 1mA I_C
	H11G1,H11G2			1.2	V	16mA I_F, 50mA I_C
	H11G3			1.2	V	20mA I_F, 50mA I_C
	Input to Output Isolation Voltage V_{ISO}	5300			V_{RMS}	See note 1
		7500			V_{PK}	See note 1
	Input-output Isolation Resistance R_{ISO}	$5x10^{10}$	10^{11}		Ω	V_{IO} = 500V (note 1)
	Input-output Capacitance Cf		0.6		pF	V = 0, f = 1MHz
	Response time (Rise), tr		100		µs	I_C = 20mA, V_{CE} = 2V,
	Response time (Fall), tf		20		µs	R_L = 100Ω

Note 1 Measured with input leads shorted together and output leads shorted together.
Note 2 Special Selections are available on request. Please consult the factory.

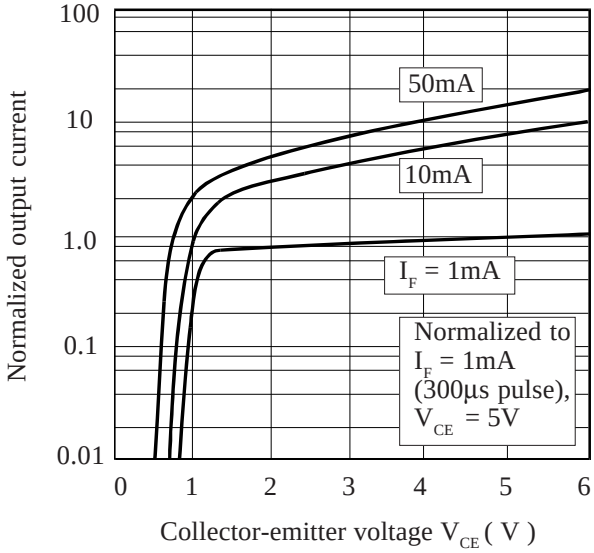
FIGURE 1



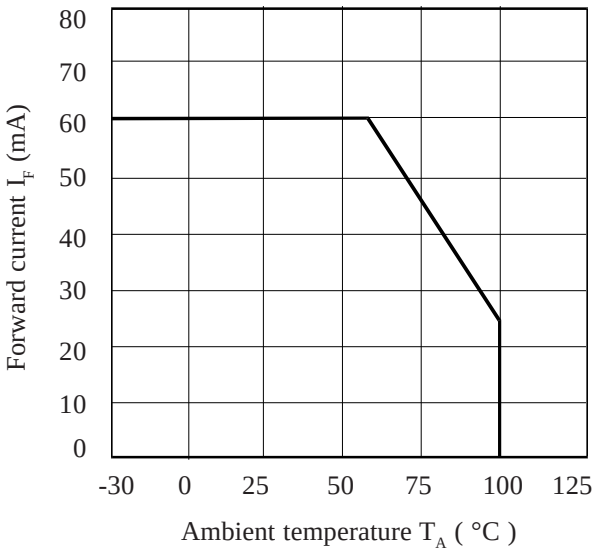
Collector Power Dissipation vs. Ambient Temperature



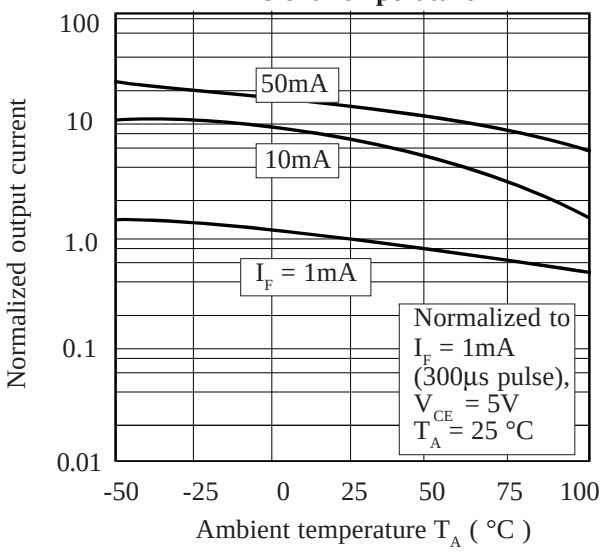
Normalized Output Current vs. Collector-emitter Voltage



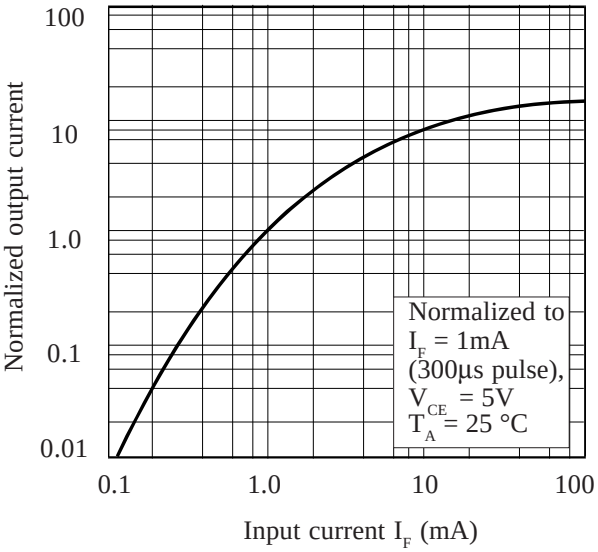
Forward Current vs. Ambient Temperature



Normalized Output Current vs. Ambient Temperature



Normalized Output Current vs. Input Current



Collector Dark Current vs. Ambient Temperature